

# NTD5413N

## Power MOSFET

### 30 Amps, 60 Volts Single N-Channel DPAK

#### Features

- Low  $R_{DS(on)}$
- High Current Capability
- Avalanche Energy Specified
- These are Pb-Free Devices

#### Applications

- LED Lighting and LED Backlight Drivers
- DC-DC Converters
- DC Motor Drivers
- Switch Mode Power Supplies
- Power Supplies Secondary Side Synchronous Rectification

#### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ Unless otherwise specified)

Parameter		Symbol	Value	Unit	
Drain-to-Source Voltage		$V_{DSS}$	60	V	
Gate-to-Source Voltage – Continuous		$V_{GS}$	$\pm 20$	V	
Gate-to-Source Voltage – Nonrepetitive ( $T_P < 10 \mu\text{s}$ )		$V_{GS}$	$\pm 30$	V	
Continuous Drain Current $R_{\theta JC}$ (Note 1)	Steady State	$I_D$	$T_C = 25^\circ\text{C}$	30	A
			$T_C = 100^\circ\text{C}$	23	
Power Dissipation $R_{\theta JC}$ (Note 1)	Steady State	$P_D$	$T_C = 25^\circ\text{C}$	68	W
Pulsed Drain Current	$t_p = 10 \mu\text{s}$	$I_{DM}$	84	A	
Operating and Storage Temperature Range		$T_J, T_{stg}$	-55 to +175	$^\circ\text{C}$	
Source Current (Body Diode)		$I_S$	30	A	
Single Pulse Drain-to-Source Avalanche Energy – Starting $T_J = 25^\circ\text{C}$ ( $V_{DD} = 50 V_{dc}, V_{GS} = 10 V, I_{L(pk)} = 30 A, L = 0.3 \text{ mH}, R_G = 25 \Omega$ )		$E_{AS}$	135	mJ	
Lead Temperature for Soldering Purposes, 1/8" from Case for 10 Seconds		$T_L$	260	$^\circ\text{C}$	

#### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Case (Drain) Steady State (Note 1)	$R_{\theta JC}$	2.2	$^\circ\text{C}/\text{W}$
	$R_{\theta JA}$	58.5	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

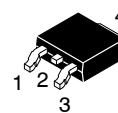
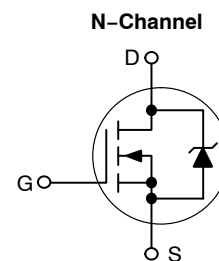
1. Surface mounted on FR4 board using 1 sq in pad size, (Cu Area 1.127 sq in [1 oz] including traces).



ON Semiconductor®

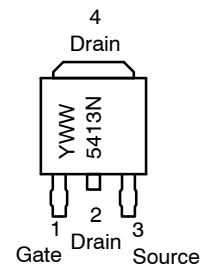
<http://onsemi.com>

$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$ (Note 1)
60 V	26 m $\Omega$ @ 10 V	30 A



DPAK  
CASE 369AA  
STYLE 2

#### MARKING DIAGRAM



5413N = Device Code  
Y = Year  
WW = Work Week  
G = Pb-Free Device

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

# NTD5413N

## ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C Unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>						
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>DS</sub> = 0 V, I <sub>D</sub> = 250 μA	60			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V <sub>(BR)DSS</sub> /T <sub>J</sub>			67.5		mV/°C
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V V <sub>DS</sub> = 60 V	T <sub>J</sub> = 25°C		1.0	μA
			T <sub>J</sub> = 150°C		50	
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±20 V			±100	nA

## ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 250 μA	2.0	3.4	4.0	V
Negative Threshold Temperature Coefficient	V <sub>GS(th)</sub> /T <sub>J</sub>			7.9		mV/°C
Drain-to-Source On-Voltage	V <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A		0.37	0.52	V
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A, 150°C		0.86		
Drain-to-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A		18.5	26	mΩ
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 20 A		36		S

## CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1 MHz		1160	1725	pF
Output Capacitance	C <sub>oss</sub>			240		
Transfer Capacitance	C <sub>rss</sub>			100		
Total Gate Charge	Q <sub>G(TOT)</sub>	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 48 V, I <sub>D</sub> = 20 A		35	46	nC
Threshold Gate Charge	Q <sub>G(TH)</sub>			1.4		
Gate-to-Source Charge	Q <sub>GS</sub>			6.5		
Gate-to-Drain Charge	Q <sub>GD</sub>			16.1		

## SWITCHING CHARACTERISTICS, V<sub>GS</sub> = 10 V (Note 3)

Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>GS</sub> = 10 V, V <sub>DD</sub> = 48 V, I <sub>D</sub> = 20 A, R <sub>G</sub> = 2.5 Ω		11		ns
Rise Time	t <sub>r</sub>			20		
Turn-Off Delay Time	t <sub>d(off)</sub>			28		
Fall Time	t <sub>f</sub>			8.0		

## DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage (Note 2)	V <sub>SD</sub>	V <sub>GS</sub> = 0 V I <sub>S</sub> = 20 A	T <sub>J</sub> = 25°C		0.87	1.2	V
			T <sub>J</sub> = 125°C		0.8		
Reverse Recovery Time	t <sub>rr</sub>	I <sub>S</sub> = 20 A <sub>dc</sub> , V <sub>GS</sub> = 0 V <sub>dc</sub> , di <sub>S</sub> /dt = 100 A/μs		52		ns	
Charge Time	t <sub>a</sub>			37			
Discharge Time	t <sub>b</sub>			15			
Reverse Recovery Stored Charge	Q <sub>RR</sub>			105.7			nC

2. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

3. Switching characteristics are independent of operating junction temperatures.

## ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
NTD5413NT4G	DPAK (Pb-Free)	2500 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# NTD5413N

## TYPICAL PERFORMANCE CURVES

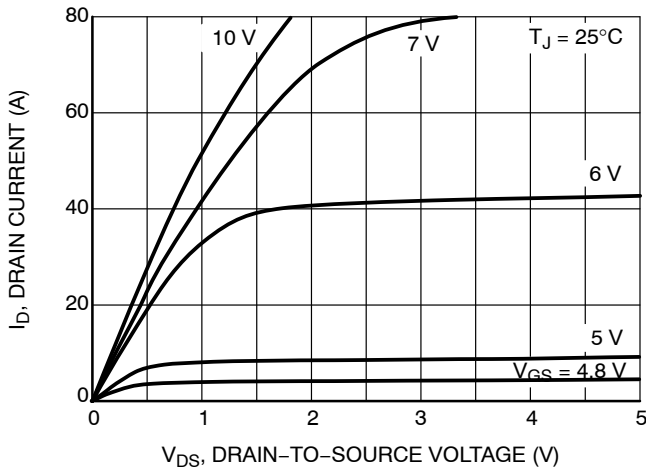


Figure 1. On-Region Characteristics

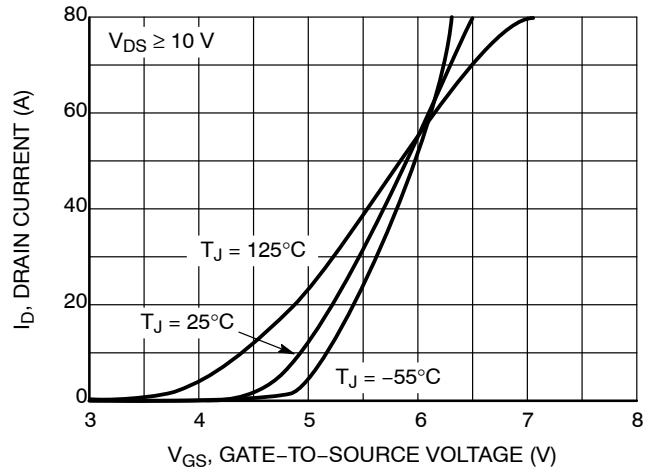


Figure 2. Transfer Characteristics

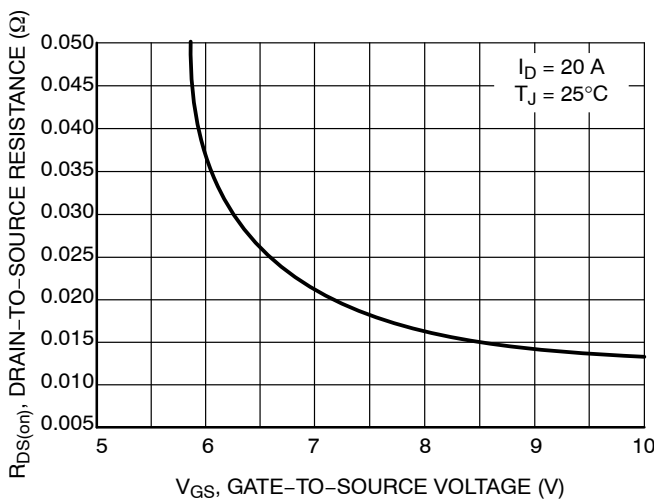


Figure 3. On-Resistance vs. Gate-to-Source Voltage

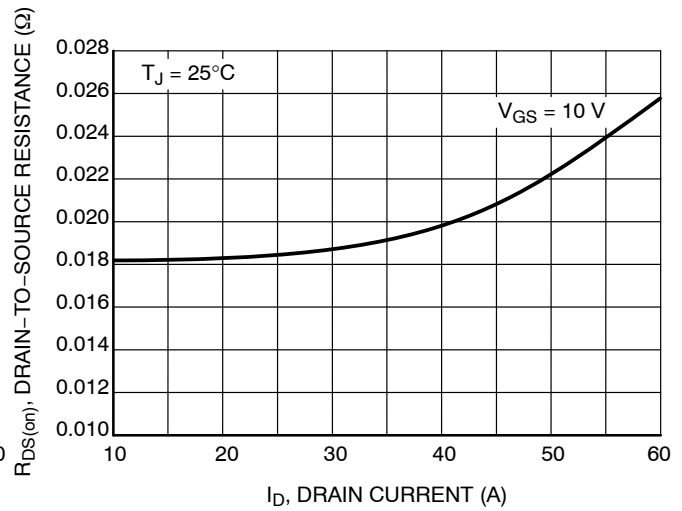


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

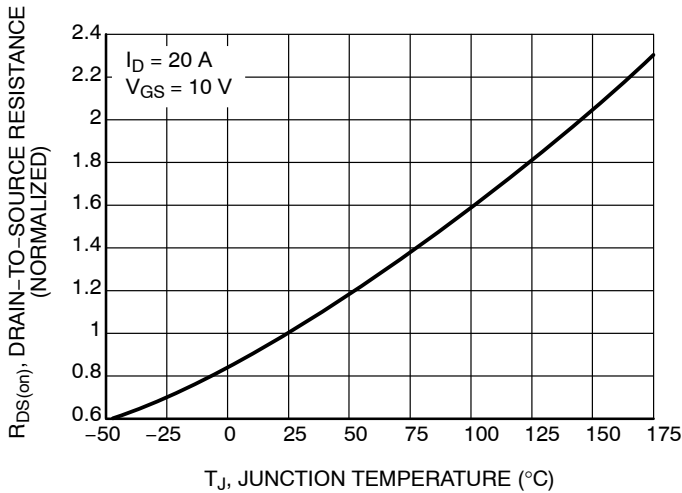


Figure 5. On-Resistance Variation with Temperature

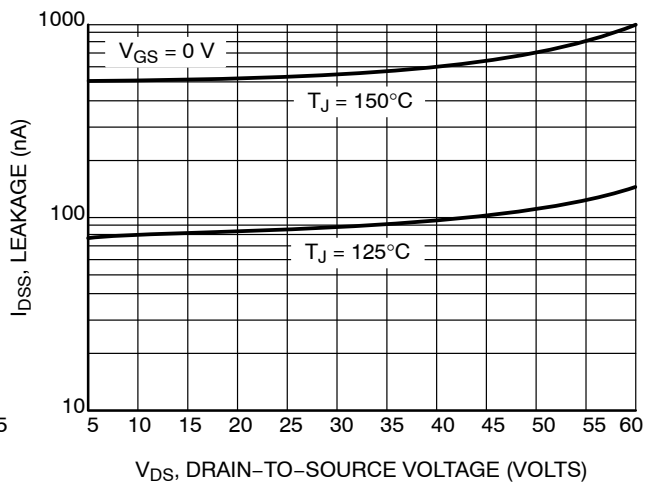


Figure 6. Drain-to-Source Leakage Current vs. Voltage

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## TYPICAL PERFORMANCE CURVES

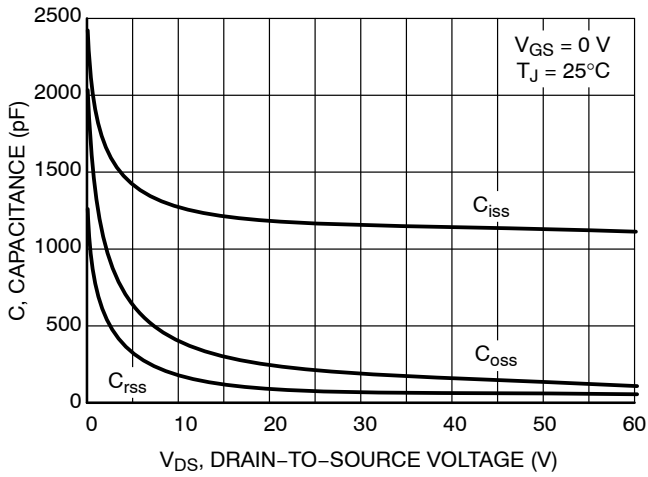


Figure 7. Capacitance Variation

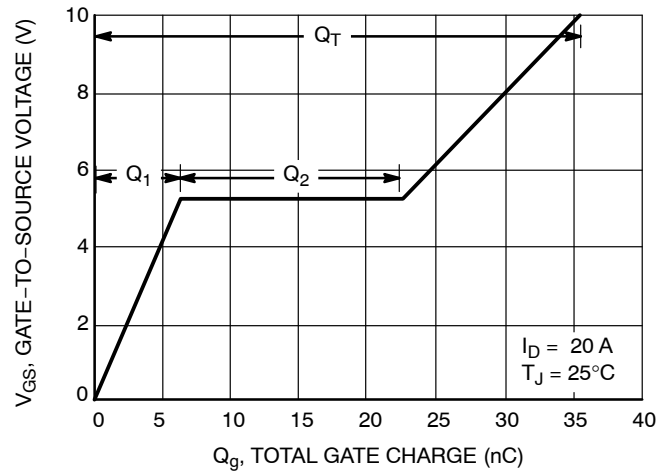


Figure 8. Gate-to-Source Voltage vs. Total Charge

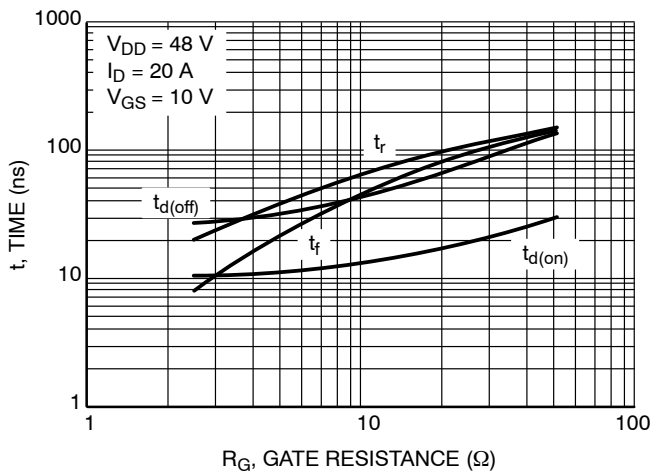


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

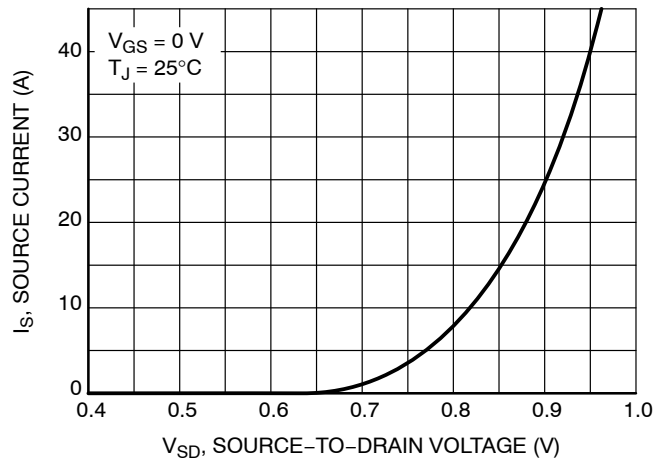


Figure 10. Diode Forward Voltage vs. Current

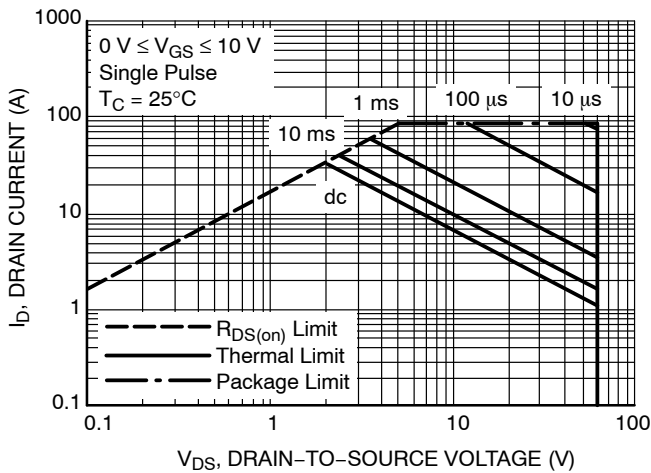


Figure 11. Maximum Rated Forward Biased Safe Operating Area

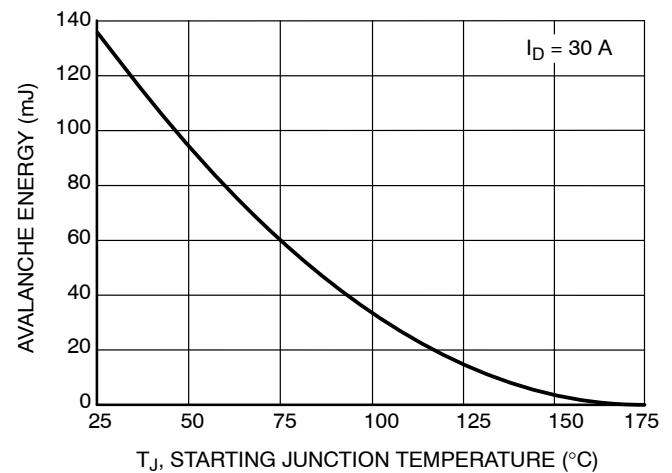


Figure 12. Maximum Avalanche Energy vs. Starting Junction Temperature

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## TYPICAL PERFORMANCE CURVES

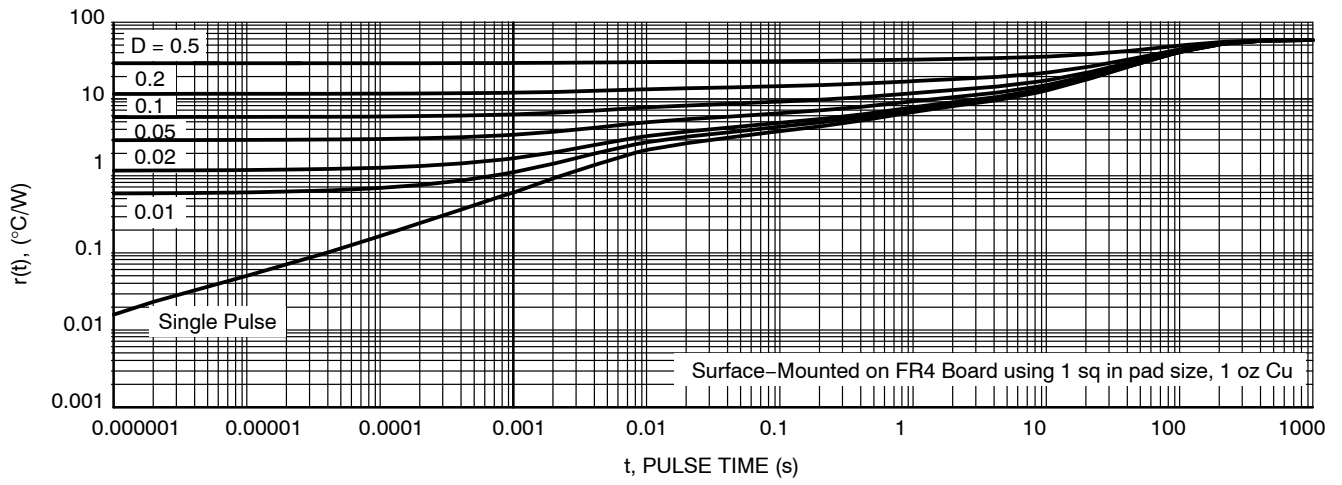
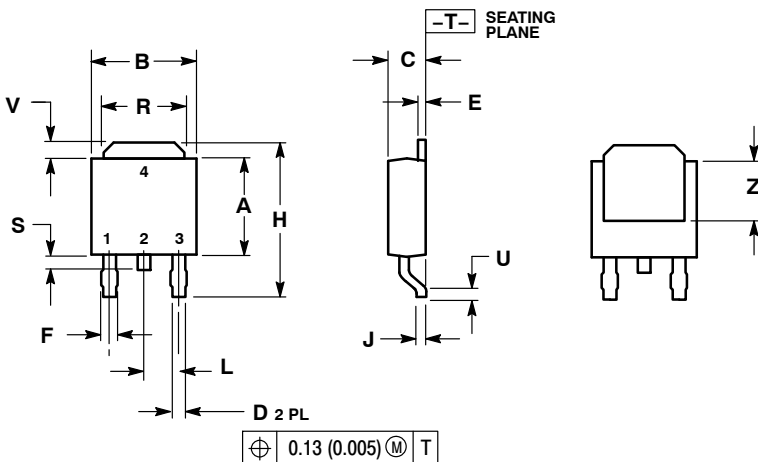


Figure 13. Thermal Response

# NTD5413N

## PACKAGE DIMENSIONS

DPAK  
CASE 369AA-01  
ISSUE A

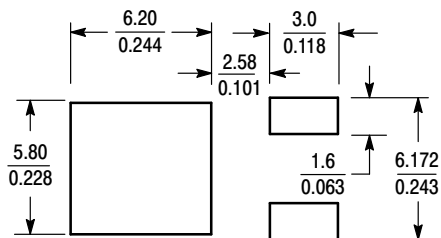


- NOTES:  
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.  
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.22
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.025	0.035	0.63	0.89
E	0.018	0.024	0.46	0.61
F	0.030	0.045	0.77	1.14
H	0.386	0.410	9.80	10.40
J	0.018	0.023	0.46	0.58
L	0.090 BSC		2.29 BSC	
R	0.180	0.215	4.57	5.45
S	0.024	0.040	0.60	1.01
U	0.020	---	0.51	---
V	0.035	0.050	0.89	1.27
Z	0.155	---	3.93	---

- STYLE 2:  
PIN 1. GATE  
2. DRAIN  
3. SOURCE  
4. DRAIN

### SOLDERING FOOTPRINT\*



SCALE 3:1 (mm/inches)

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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